

# Plastic Medium-Power Silicon NPN Transistors

## BD135G, BD137G, BD139G

This series of plastic, medium-power silicon NPN transistors are designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

### Features

- High DC Current Gain
- BD 135, 137, 139 are complementary with BD 136, 138, 140
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BD135G BD137G BD139G	$V_{CEO}$	45 60 80	Vdc
Collector-Base Voltage BD135G BD137G BD139G	$V_{CBO}$	45 60 100	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current	$I_C$	1.5	Adc
Base Current	$I_B$	0.5	Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.25 10	Watts mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	12.5 100	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

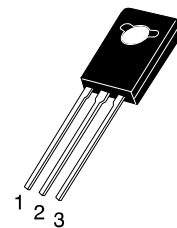
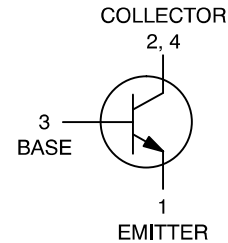
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	10	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	100	$^\circ\text{C/W}$

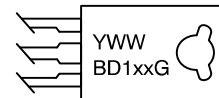
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 1.5 A POWER TRANSISTORS NPN SILICON 45, 60, 80 V, 12.5 W



TO-225  
CASE 77-09  
STYLE 1

### MARKING DIAGRAM



- Y = Year
- WW = Work Week
- BD1xx = Device Code  
xx = 35, 37, 39
- G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping
BD135G	TO-225 (Pb-Free)	500 Units / Box
BD137G	TO-225 (Pb-Free)	500 Units / Box
BD139G	TO-225 (Pb-Free)	500 Units / Box

### DISCONTINUED (Note 1)

Device	Package	Shipping
BD135TG	TO-225 (Pb-Free)	50 Units / Rail

1. **DISCONTINUED:** These devices are not recommended for new design. Please contact your onsemi representative for information. The most current information on these devices may be available on [www.onsemi.com](http://www.onsemi.com).

## BD135G, BD137G, BD139G

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage* (I <sub>C</sub> = 0.03 Adc, I <sub>B</sub> = 0) BD135G BD137G BD139G	BV <sub>CEO</sub> *	45 60 80	– – –	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0, T <sub>C</sub> = 125°C)	I <sub>CBO</sub>	– –	0.1 10	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	10	μAdc
DC Current Gain (I <sub>C</sub> = 0.005 A, V <sub>CE</sub> = 2 V) (I <sub>C</sub> = 0.15 A, V <sub>CE</sub> = 2 V) (I <sub>C</sub> = 0.5 A, V <sub>CE</sub> = 2 V)	h <sub>FE</sub> *	25 40 25	– 250 –	–
Collector–Emitter Saturation Voltage* (I <sub>C</sub> = 0.5 Adc, I <sub>B</sub> = 0.05 Adc)	V <sub>CE(sat)</sub> *	–	0.5	Vdc
Base–Emitter On Voltage* (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 2.0 Vdc)	V <sub>BE(on)</sub> *	–	1	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

\*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

### TYPICAL CHARACTERISTICS

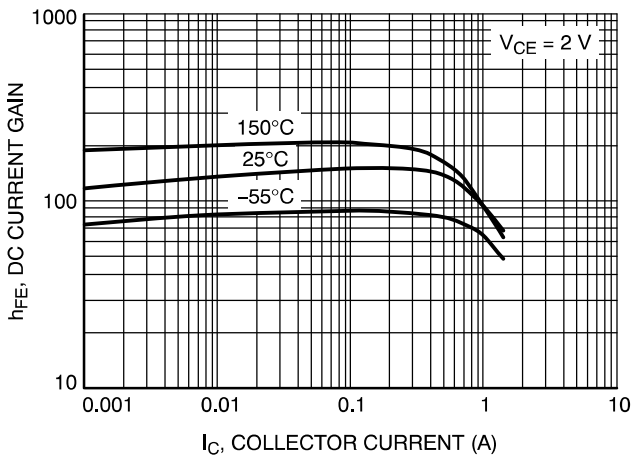


Figure 1. DC Current Gain

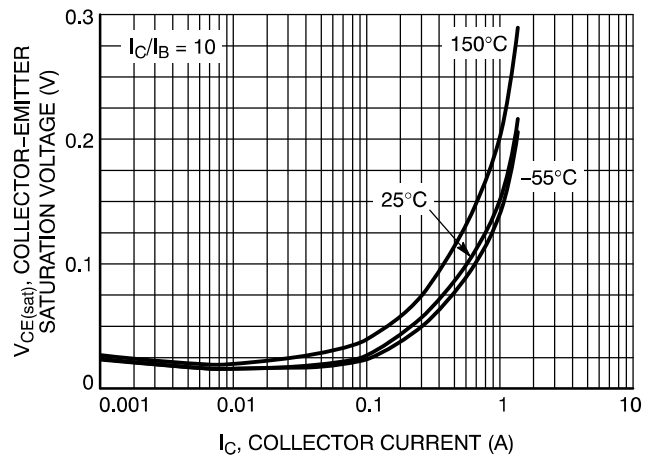


Figure 2. Collector–Emitter Saturation Voltage

# BD135G, BD137G, BD139G

## TYPICAL CHARACTERISTICS

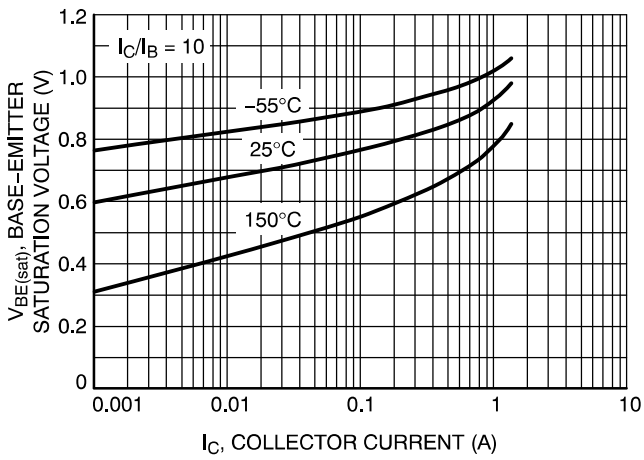


Figure 3. Base-Emitter Saturation Voltage

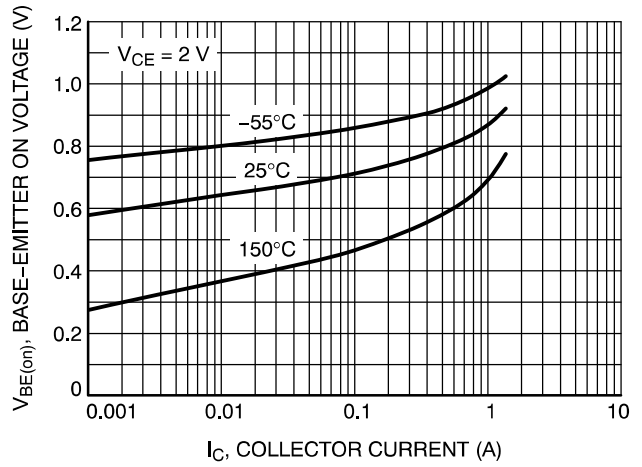


Figure 4. Base-Emitter On Voltage

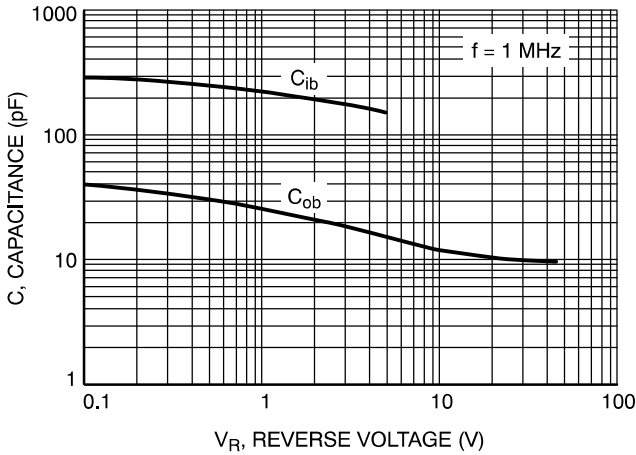


Figure 5. Capacitance

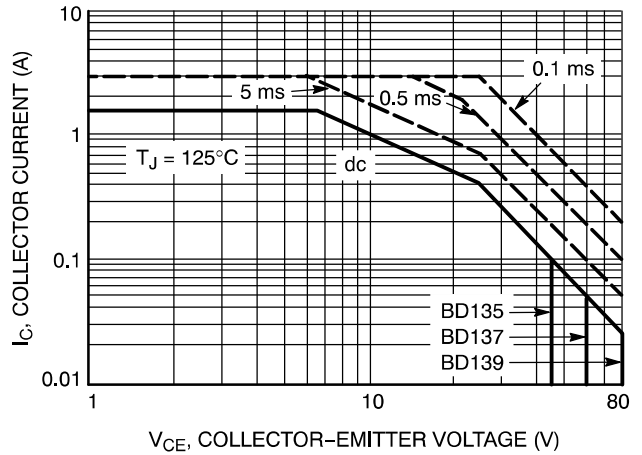


Figure 6. Active-Region Safe Operating Area

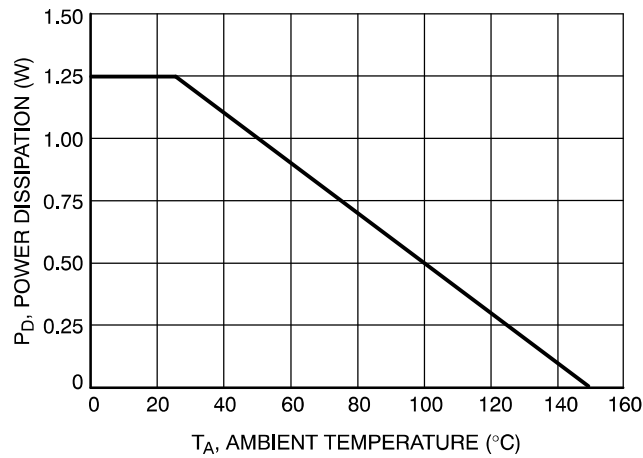
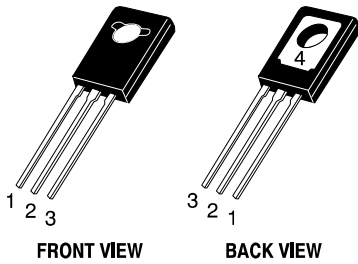


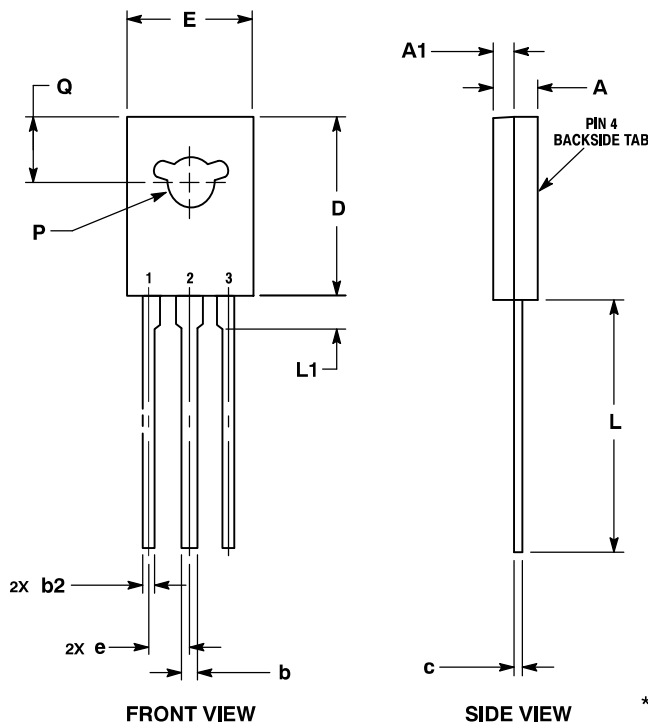
Figure 7. Power Derating

**TO-225**  
**CASE 77-09**  
**ISSUE AD**

DATE 25 MAR 2015



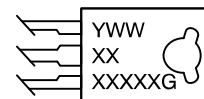
SCALE 1:1



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. NUMBER AND SHAPE OF LUGS OPTIONAL.

DIM	MILLIMETERS	
	MIN	MAX
A	2.40	3.00
A1	1.00	1.50
b	0.60	0.90
b2	0.51	0.88
c	0.39	0.63
D	10.60	11.10
E	7.40	7.80
e	2.04	2.54
L	14.50	16.63
L1	1.27	2.54
P	2.90	3.30
Q	3.80	4.20

**GENERIC MARKING DIAGRAM\***



- Y = Year
- WW = Work Week
- XXXXX = Device Code
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- |   |   |   |   |   |
|---|---|---|---|---|
| <p>STYLE 1:<br/>PIN 1. EMITTER<br/>2., 4. COLLECTOR<br/>3. BASE</p> | <p>STYLE 2:<br/>PIN 1. CATHODE<br/>2., 4. ANODE<br/>3. GATE</p> | <p>STYLE 3:<br/>PIN 1. BASE<br/>2., 4. COLLECTOR<br/>3. EMITTER</p> | <p>STYLE 4:<br/>PIN 1. ANODE 1<br/>2., 4. ANODE 2<br/>3. GATE</p> | <p>STYLE 5:<br/>PIN 1. MT 1<br/>2., 4. MT 2<br/>3. GATE</p>     |
| <p>STYLE 6:<br/>PIN 1. CATHODE<br/>2., 4. GATE<br/>3. ANODE</p>     | <p>STYLE 7:<br/>PIN 1. MT 1<br/>2., 4. GATE<br/>3. MT 2</p>     | <p>STYLE 8:<br/>PIN 1. SOURCE<br/>2., 4. GATE<br/>3. DRAIN</p>      | <p>STYLE 9:<br/>PIN 1. GATE<br/>2., 4. DRAIN<br/>3. SOURCE</p>    | <p>STYLE 10:<br/>PIN 1. SOURCE<br/>2., 4. DRAIN<br/>3. GATE</p> |

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